

PROCEEDINGS OF SPIE

Light-Emitting Diodes: Materials, Devices, and Applications for Solid State Lighting XX

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15–17 February 2016
San Francisco, California, United States

Sponsored and Published by
SPIE

Volume 9768

Proceedings of SPIE 0277-786X, V. 9768

SPIE is an international society advancing an interdisciplinary approach to the science and application of light.

Light-Emitting Diodes: Materials, Devices, and Applications for Solid State Lighting XX, edited by Heonsu Jeon,
Li-Wei Tu, Michael R. Krames, Martin Strassburg, Proc. of SPIE Vol. 9768, 976801 · © 2016 SPIE
CCC code: 0277-786X/16/\$18 · doi: 10.1117/12.2239988

Proc. of SPIE Vol. 9768 976801-1

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Author(s), "Title of Paper," in *Light-Emitting Diodes: Materials, Devices, and Applications for Solid State Lighting XX*, edited by Heonsu Jeon, Li-Wei Tu, Michael R. Krames, Martin Strassburg, Proceedings of SPIE Vol. 9768 (SPIE, Bellingham, WA, 2016) Six-digit Article CID Number.

ISSN: 0277-786X
ISSN: 1996-756X (electronic)
ISBN: 9781510600034

Published by

SPIE

P.O. Box 10, Bellingham, Washington 98227-0010 USA
Telephone +1 360 676 3290 (Pacific Time) · Fax +1 360 647 1445
SPIE.org

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